

AMENDMENTS TO THE SPECIFICATION:

Page 3, replace the paragraph beginning on line 10 and bridging pages 3 and 4 with the following amended paragraph:

--Recently, there has been proposed a process in which ~~comprises growing, on a substrate,~~ a thick GaN film is grown hetero-epitaxially on ~~the~~ a substrate by means of HVPE method (hydride vapor phase epitaxial growth method) and then the substrate is removed therefrom to obtain a GaN self-supported substrate. However, regarding this process, there has not yet been developed ~~[[yet]]~~ such a technique that the GaN grown on the sapphire substrate ~~would~~ can be separated from the sapphire substrate by etching. There have been ~~attempt~~ attempts to employ a method of mechanically removing the sapphire substrate by polishing; however, it has been found that breakage of substrate may result from an increased ~~warp~~ warp of substrate which is occasionally induced during the polishing, and therefore the process has not been reached the level of practical use. In Jpn. J. Appl. Phys. Vol. 38 (1999) Pt. 2, No. 3A L217 to L219 is reported a process in which GaN is grown up to a thick thickness on a sapphire substrate by a HVPE method and then laser pulses are irradiated thereon to peel off only the GaN layer therefrom. However, even as for this process, there remains a problem that the substrate tends to crack easily. In JP-A-2000-12900 is disclosed a process with a easily removable substrate, such as a process in which GaN is grown up to a thick thickness on a GaAs

substrate by a HVPE method and then the GaAs substrate is etched to be removed ~~away~~ therefrom. With this process, a large size GaN substrate can be obtained at a relatively high yield; however, there is such a problem to be solved that the ~~decomposition of~~ GaAs substrate ~~is progressed~~ decomposes during the growth of the GaN crystal, and thus As ~~resulted~~ will be incorporated into the GaN as a contaminant. Selective growth using a patterned mask, such as FIELO mentioned above, is effective in order to reduce the defect density in epitaxially grown GaN, and there are disclosed techniques such as that proposed in JP-A-H10-312971. These techniques, however, have not yet been applied in practical production of self-supported GaN substrate because there has been no technique for easy peeling ~~of~~ off the substrate.--

Page 12, replace the paragraph beginning on line 20 with the following amended paragraph:

--The growth temperature for the first group III nitride semiconductor layer is preferably in range of 400°C or ~~high~~ higher but 800°C or lower. By selecting such a condition, it is possible to preferably grow a group III nitride semiconductor layer on the metal element-containing film. As mentioned above, in case that a metal film composed of a single metal alone is used as the metal element-containing film, growth of a group III nitride semiconductor layer thereon is difficult

~~in usual~~; however, with use of such a low growth temperature, ~~it~~
the layer can be ~~layer-grown~~ grown stably[[],].--